

Form PTO 1449 Rev. 7-80 <b>U.S. Department of Commerce Patent and Trademark Office</b> <b>LIST OF PRIOR ART CITED BY APPLICANT</b> (Use Several Sheets If Necessary)	Atty. Docket No. CH8498US	Serial No. To Be Assigned
	Applicant Jagdish Narayan et al	
	Filing Date Herewith	Group No.

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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	AC	4,036,708	07/19/77	Feit et al	204	38	
	AD	5,281,485	01/25/94	Colgan et al	428	457	
	AE	5,406,123	04/11/95	Narayan	257	767	
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	AH	6,291,885 B1	09/18/01	Cabral, Jr. et al	257	751	
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	AS	Materials Science and Engineering, R19 (month unavailable) 1997, pages 87-151, Shyam P. Murarka "Multilevel interconnections for ULSI and GSI era"
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	AS	Acta Metallurgica, Vol 25, (month unavailable) 1977, pages 1485-1490, S. Takeuchi et al, "Slip in High Purity Tantalum Between 0.7 and 40 K"
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